

Product Summary

V _{(BR)DSS}	R _{DS(on)TYP}	I _D		
150V	13mΩ@10V	55A		



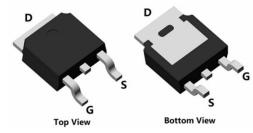
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

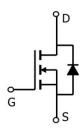
- Power switching application
- DC-DC Converter
- Power Management

Package

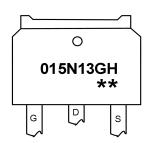


TO-252(1:G 2:D 3:S)

Circuit diagram



Marking



015N13GH : Product code ** : Week code

Order Information

Device	Package	Unit/Tube	
SP015N13GHTH	TO-252	2500	



150V N-Channel Power MOSFET

Absolute maximum ratings (Ta=25°C,unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current (Tc=25°C)	I _D	55	Α
Continuous Drain Current (Tc=100°C)	I _D	38	Α
Pulsed Drain Current	I _{DM}	220	Α
Single Pulse Avalanche Energy ¹	Eas	272	mJ
Power Dissipation (Tc=25°C)	P _D	135	W
Thermal Resistance Junction-to-Case	R _{θJC}	0.93	°C/W
Storage Temperature Range	T _{STG}	-55 to 150	$^{\circ}$
Operating Junction Temperature Range	TJ	-55 to 150	$^{\circ}$

Electrical characteristics (Ta=25°C, unless otherwise noted)

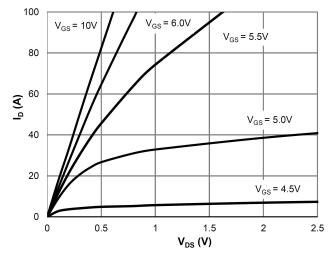
Characteristics	Symbol	Test Condition	Min	Тур	Max	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	ID = 250µA, VGS = 0V	150	-	-	V	
Drain Cut-Off Current	I _{DSS}	VDS = 120V, VGS = 0V	-	-	1		
Gate Leakage Current	I _{GSS}	VGS = ±20V, VDS = 0V	-	-	±0.1	μA	
Gate Threshold Voltage	$V_{GS(th)}$	VDS = VGS, ID = 250μA	2.0	3.0	4.0	V	
Drain-Source ON Resistance	R _{DS(ON)}	VGS = 10V, ID = 20A	-	13	16	mΩ	
Dynamic Characteristics							
Input Capacitance	Ciss		-	2230	-		
Output Capacitance	Coss	VDS = 75V, VGS = 0V, f = 1.0MHz	-	293	-	pF	
Reverse Transfer Capacitance	C _{rss}		-	22	-		
Total Gate Charge	Qg		-	30	-	nC	
Gate-Source Charge	Q _{gs}	VDS=75V , VGS=10V , ID=20A	-	5.8	-		
Gate-Drain Charge	Q_{gd}		-	7	-		
Switching Characteristics							
Turn-On Delay Time	t _{d(on)}		-	13	-		
Rise Time	tr	VGS = 10V, VDS = 50V, ID =20A	-	25	-		
Turn-Off Delay Time	t _{d(off)}	RG = 6Ω	-	31	-	nS	
Fall Time	t _f		-	25	-		
Drain-Source Body Diode Characteris	tics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 1A, VGS = 0V	-	-	1.2	V	
Maximum Body-Diode Continuous Current	Is		-	-	55	Α	
Body Diode Reverse Recovery Time	Trr	 20∆ di/dt-100∆/us TI-25°C	-	65	-	nS	
Body Diode Reverse Recovery Charge	Qrr	I _S =20A, di/dt=100A/us, TJ=25℃		180	-	nC	

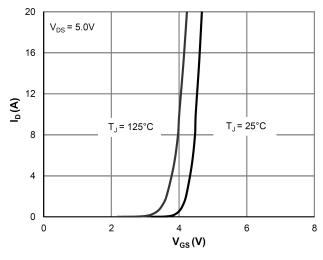
Note:

1. The test condition is VDD=50V,VGS=10V,L=0.5mH,RG=25 Ω ;

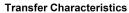


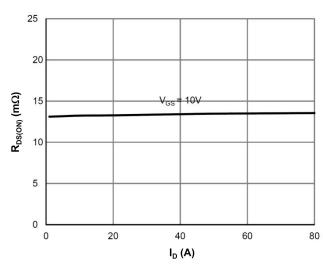
Typical Characteristic

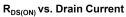


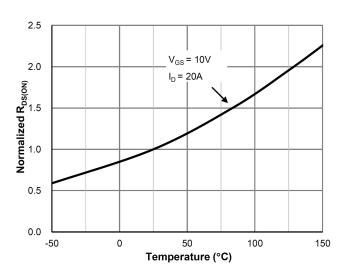


Saturation Characteristics

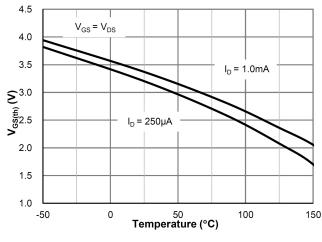


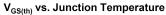


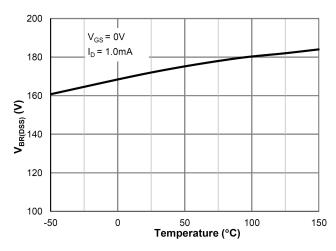




R_{DS(ON)} vs. Junction Temperature

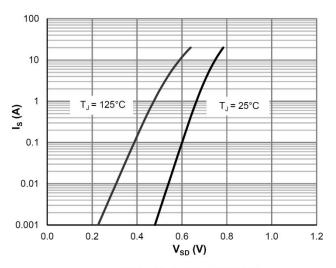


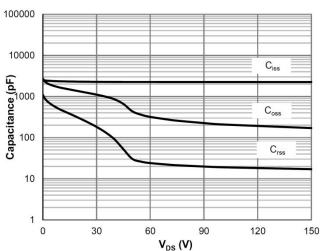




 $V_{\mathrm{BR}(\mathrm{DSS})}$ vs. Junction Temperature

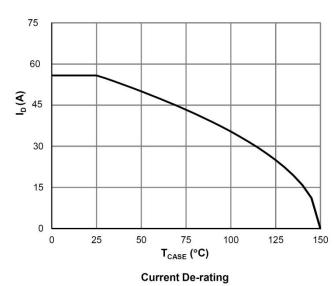


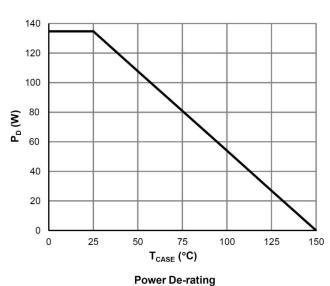


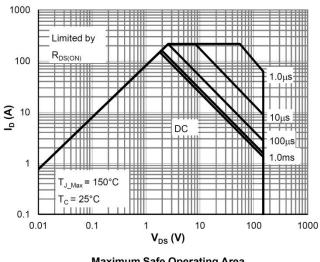


Body-Diode Characteristics

Capacitance Characteristics





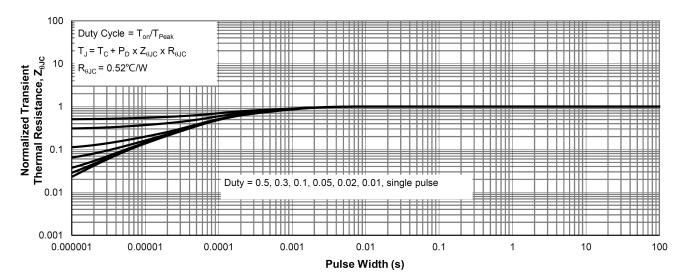


1200 900 **8** 600 300 0 0.00001 0.0001 0.001 0.01 0.1 Pulse Width (s)

Maximum Safe Operating Area

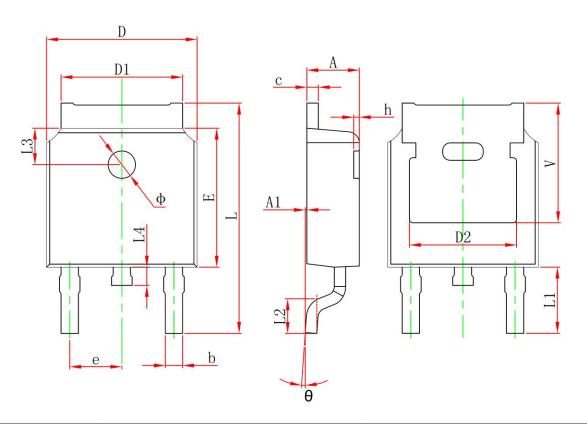
Single Pulse Power Rating, Junction-to-Case





Normalized Maximum Transient Thermal Impedance

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830	4.830 REF.		REF.	
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 REF.		0.114 REF.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063 REF.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 REF.		0.211 REF.		